

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Satoshi INOUE; Tatsuya SHIMODA

Serial No.: Rule 53(b) Divisional of Reissue Application No. 10/263,070 filed October 3, 2002
(which is a Reissue of U.S. Patent No. 6,127,199 issued October 3, 2000)

Filed: December 31, 2003

For: MANUFACTURING METHOD OF ACTIVE MATRIX SUBSTRATE, ACTIVE
MATRIX SUBSTRATE AND LIQUID CRYSTAL DISPLAY DEVICE

Docket No.: 040852.98

INFORMATION DISCLOSURE STATEMENT

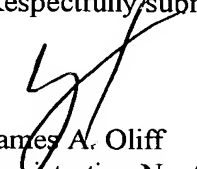
Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. All of the references were cited by or submitted to the Office in parent application No. 10/263,070, filed October 3, 2002, of which this application is a divisional. Thus, copies of these references are not attached. 37 CFR §1.98(d).

Respectfully submitted,


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<p>DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461</p>

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 040852.98		APPLICATION NO. Rule 53(b) Divisional of Application No. 10/263,070	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT(S) Satoshi INOUE; Tatsuya SHIMODA			
				FILING DATE December 31, 2003			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
		5,747,121	05/1998	Okazaki et al.			
		5,767,930	06/1998	Kobayashi et al.			
		5,807,772	09/1998	Takemura			
		5,888,839	03/1999	Ino et al.			
		5,468,521	11/1995	Kanai et al.			
		5,008,218	04/1991	Kawachi et al.			
		5,693,541	12/1997	Yamazaki et al.			
		5,589,962	12/1996	Yamamoto et al.			
		5,527,649	06/1996	Sato et al.			
		5,926,735	07/1999	Yamazaki et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
		JP-A-6-291291	10/1994	JAPAN			
		JP-A-8-288522	11/1996	JAPAN			
		JP-A-61-231714	10/1986	JAPAN			
		JP-A-8-62591	03/1996	JAPAN			
		WO 98/09333	03/1998	WIPO			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
		Sameshima, T. "Laser Beam Application to Thin Film Transistors," <u>Applied Surface Science</u> 96-98, (1996), pp. 352-358.					
EXAMINER					DATE CONSIDERED		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: December 31, 2003